

SSCP3906GS9

PNP Switching Transistor

Features

VCB	VCE	VBE	IC
-40V	-40V	-5V	-200mA

Description

The PNP Transistor is designed for use in linear and switching applications. The device is housed in the SOT-723 package, which is designed for telephony and professional communication equipment.

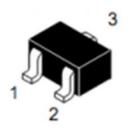
Applications

- General purpose switching and amplification
- Telephony and professional communication equipment

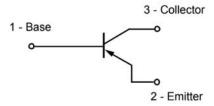
> Ordering Information

Device	Package	Shipping
SSCP3906GS9	SOT-723	8000/Reel

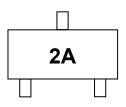
Pin configuration



SOT-723



Circuit Diagram



Marking (Top View)



ightarrow Absolute Maximum Ratings(T_A=25°C unless otherwise noted)

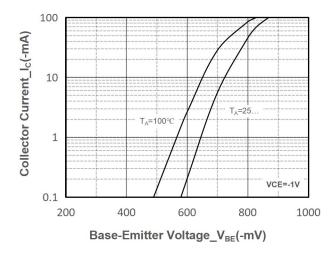
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector- Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current-Continuous	Ic	-200	mA
Collector Power Dissipation	Pc	200	mW
Junction Temperature	TJ	150	$^{\circ}$
Storage Temperature	T _{STG}	-55 to 150	$^{\circ}$

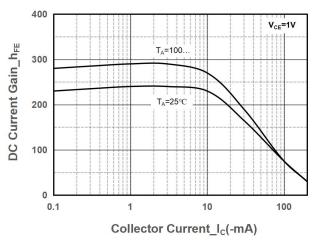
➤ Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-10uA,I _E =0	-40			V
Collector-emitter Breakdown Voltage	BV _{CEO}	I _C =-1mA,I _B =0	-40			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E =-10uA,I _C =0	-5			V
Collector Cutoff Current	I _{CEX}	V _{CE} =-30V, V _{EB} =-3V			-50	nA
Collector Cutoff Current	I _{CBO}	V _{CB} =-30V,I _E =0			-100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =-3V,I _C =0			-100	nA
		V _{CE} =-1V,I _C =-10mA	100		300	
DC Current Gain	h _{FE}	V _{CE} =-1V,I _C =-0.1mA	60			
		V _{CE} =-1V,I _C =-100mA	30			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I_C =-50mA, I_B =-5mA			-0.4	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-50mA,I _B =-5mA			-0.95	V
Transition frequency	f⊤	V _{CE} =-20V,I _C =-10mA f=100MHz	250			MHz
Delay Time	t _d	V _{CC} =-3V,V _{BE} =0.5V			35	ns
Rise Time	t _r	I _C =-10mA,I _{B1} =-1mA			35	ns
Storage Time	ts	V _{CC} =-3V,I _C =-10mA			225	ns
Fall Time	t _f	I _{B1} =-I _{B2} =-1mA			75	ns



\succ Typical Performance Characteristics (T_A=25°C unless otherwise noted)





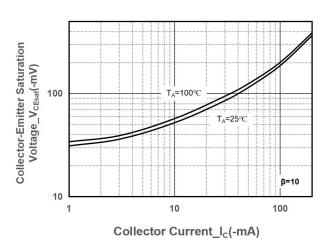
Collector Current vs. Base-Emitter Voltage

1000
900
900
1 T_A=25°C
T_A=25°C
T_A=100°C

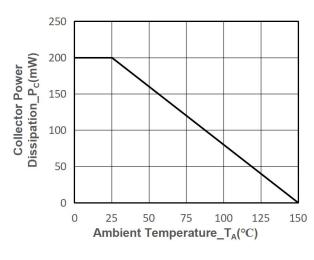
1 10 100

Collector Current_I_C(-mA)

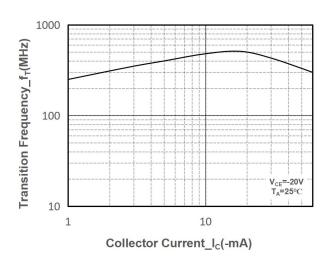
DC Current Gain vs. Collector Current



V_{BE(sat)} vs. Collector Current



V_{CE(sat)} vs. Collector Current

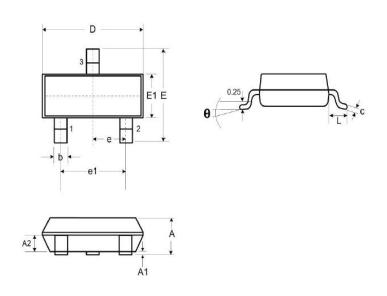


Power derating vs. Ambient temperature

Transition Frequency vs. Collector Current

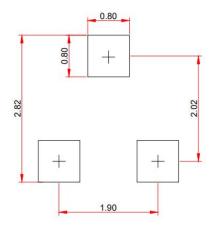


> Package Information



DIM	Millimeters			
	Min.	Тур.	Max.	
Α	0.89	-	1.12	
A 1	0.01	1	0.10	
A2	0.88	0.95	1.02	
b	0.30	-	0.51	
С	0.08	ı	0.18	
D	2.80	2.90	3.04	
E	2.10	2.37	2.64	
E1	1.20	1.30	1.40	
е		0.95		
e1	1.90			
L	0.40	0.50	0.60	
L1	0.55			
N	3			
θ	0°	-	8°	

Recommended Pad outline (Unit: mm)





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